

ABSTRACT

A gate driver for forcing a power transistor including a gate electrode insulated with oxide film into conduction or shut-off, the gate driver includes a first current source for outputting a first current value to raise an electric potential of the gate electrode for changing shut-off state of the power transistor to conductive state; and a second current source for outputting a second current value to lower the electric potential of the gate electrode for changing the conductive state of the power transistor to the shut-off state. The first current value and the second current value are assigned based on at least one kind of current-source control information. This structure allows preparing an appropriate speed of forcing the power transistor into conduction or shut-off with a small number of elements, and the gate driver can be used with ease for driving power transistors having different output sizes.